2SD2018

Silicon NPN epitaxial planar type darlington

For low-frequency amplification

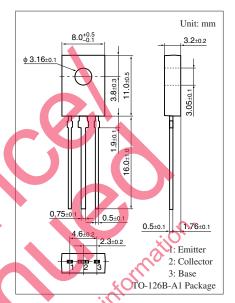
■ Features

- High forward current transfer ratio h_{FE}
- Built-in 60 V Zener diode between base to collector

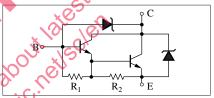
■ Absolute Maximum Ratings $T_a = 25$ °C

Symbol	Rating	Unit	
) V _{CBO}	-10	V	
) V _{CEO}	60 +25	V	
) V _{EBO}	5	V	
I_{C}	1	A	
I_{CP}	1.5	A	
P _C	1.2	W	
	5.0		
T _j	150	°C	
T _{stg}	-55 to +150	°C	
1	V _{CBO} V _{CEO} V _{CEO} V _{EBO} I _C I _{CP} T _j	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	

Note) *: With a 100 mm \times 100 mm \times 2 mm Al heat sick.



Internal Connection



■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 100 \mu{\rm A}, I_{\rm E} = 0$	50		85	V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	50		85	V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CR} = 25 \text{ V}, I_{P} = 0$			1	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = 4V, I_C = 0$			2	mA
Forward current transfer ratio *	h_{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ A}$	6500		40 000	_
Collector-emitter saturation voltage *	V _{CE(sat)}	$I_C = 1.0 \text{ A}, I_B = 1.0 \text{ mA}$			1.8	V
Base-emitter saturation voltage *	V _{BE(sat)}	$I_C = 1.0 \text{ A}, I_B = 1.0 \text{ mA}$			2.2	V

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

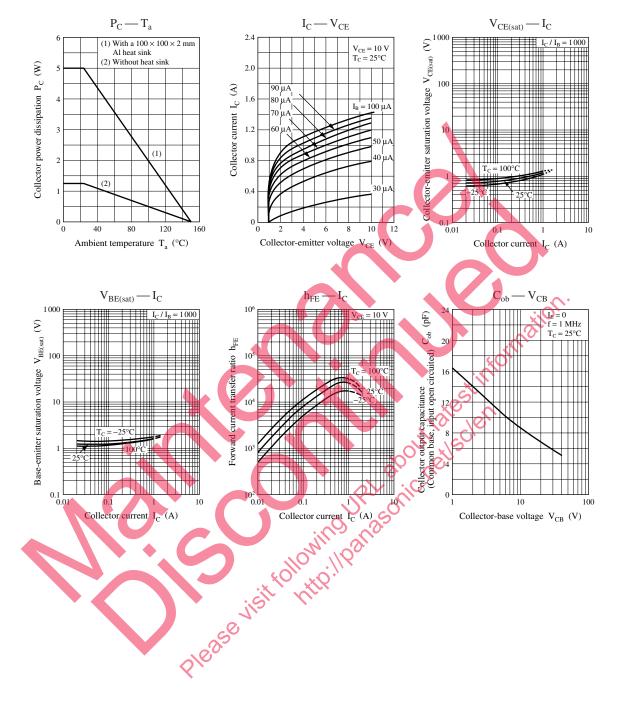
2. *: Pulse measurement

0.1 0.01

Collector current I_C (A)

Panasonic

Collector-base voltage V_{CB} (V)



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